HIGH-SPEED 3.3V 256K x 36 DT **SYNCHRONOUS BANK-SWITCHABLE DUAL-PORT STATIC RAM** WITH 3.3V OR 2.5V INTERFACE

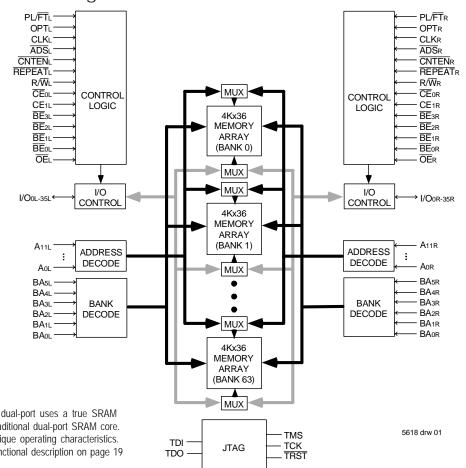
IDT70V7519S

LEAD FINISH (SnPb) ARE IN EOL PROCESS - LAST TIME BUY EXPIRES JUNE 15, 2018

Features:

- 256K x 36 Synchronous Bank-Switchable Dual-ported **SRAM Architecture**
 - 64 independent 4K x 36 banks
 - 9 megabits of memory on chip
- Bank access controlled via bank address pins
- High-speed data access
 - Commercial: 3.4ns(200MHz)/3.6ns (166MHz)/4.2ns (133MHz) (max.)
- Industrial: 3.6ns (166MHz)/4.2ns (133MHz) (max.)
- Selectable Pipelined or Flow-Through output mode
- Counter enable and repeat features
- Dual chip enables allow for depth expansion without additional logic
- Full synchronous operation on both ports
- 5ns cycle time, 200MHz operation (14Gbps bandwidth)
- Fast 3.4ns clock to data out
- Functional Block Diagram

- 1.5ns setup to clock and 0.5ns hold on all control, data, and _ address inputs @ 200MHz
- Data input, address, byte enable and control registers
- Self-timed write allows fast cycle time
- ٠ Separate byte controls for multiplexed bus and bus matching compatibility
- LVTTL- compatible, 3.3V (±150mV) power supply for core
- LVTTL compatible, selectable 3.3V (±150mV) or 2.5V (±100mV) power supply for I/Os and control signals on each port
- ٠ Industrial temperature range (-40°C to +85°C) is available at 166MHz and 133MHz
- Available in a 208-pin Plastic Quad Flatpack (PQFP), 208-pin fine pitch Ball Grid Array (fpBGA), and 256-pin Ball Grid Array (BGA)
- Supports JTAG features compliant with IEEE 1149.1
- ٠ Green parts available, see ordering information



NOTE:

1. The Bank-Switchable dual-port uses a true SRAM core instead of the traditional dual-port SRAM core. As a result, it has unique operating characteristics. Please refer to the functional description on page 19 for details

JUNE 2015

High-Speed 256K x 36 Synchronous Bank-Switchable Dual-Port Static RAM

Industrial and Commercial Temperature Ranges

Description:

The IDT70V7519 is a high-speed 256Kx36 (9Mbit) synchronous Bank-Switchable Dual-Ported SRAM organized into 64 independent 4Kx36 banks. The device has two independent ports with separate control, address, and I/O pins for each port, allowing each port to access any 4Kx36 memory block not already accessed by the other port. Accesses by the ports into specific banks are controlled via the bank address pins under the user's direct control.

Registers on control, data, and address inputs provide minimal setup and hold times. The timing latitude provided by this approach allows systems to be designed with very short cycle times. With an input data register, the IDT70V7519 has been optimized for applications having unidirectional or bidirectional data flow in bursts. An automatic power down feature, controlled by CE0 and CE1, permits the on-chip circuitry of each port to enter a very low standby power mode. The dual chip enables also facilitate depth expansion.

The 70V7519 can support an operating voltage of either 3.3V or 2.5V on one or both ports, controllable by the OPT pins. The power supply for the core of the device(VDD) remains at 3.3V. Please refer also to the functional description on page 19.

A1 IO19L	a2 IO18L	^{A3} Vss	^{A4} TDO	A5 NC	A6 BA4L	A7 BA0L	A8 A8L	A9 BE1L	a10 Vdd	A11 CLKL	A12 CNTENL	A13 A4L	A14 A0L	A15 OPTL	a16 I∕O17∟	A17 Vss
B1 I/O20R	^{B2} Vss	B3 I/O18R	^{B4} TDI	^{B5} BA5l	B6 BA1L	B7 A9L	B8 BE2L	B9 CEOL	^{B10} Vss	^{B11} ADSL	B12 A5L	B13 A1L	B14 Vss	^{b15} Vddqr	в16 I/O16L	B17 I/O15
c1 Vddql	C2 I/O19R	C3 Vddqr	C4 PL/FTL	^{C5} NC	C6 BA2L	C7 A10L	C8 BE3L	C9 CE1L	C10 Vss	C11 R/₩L	C12 A6L	C13 A2L	C14 VDD	C15 I/O16R	C16 I/O15L	C17 Vss
D1 I/O22L	D2 Vss	d3 I/O21L	d4 I/O20l	d5 BA3l	D6 A11L	d7 A7l	D8 BE0L	d9 Vdd	D10 OEL	d11 Repeatl	D12 A3L	d13 Vdd	D14 I/O17R	d15 Vddql	D16 I/O14L	D17 I/O14F
e1 I/O23L	e2 I/O22r	e3 Vddqr	e4 I/O21r											e15 I/O13r	^{E16} Vss	e17 I/O13L
f1 Vddql	f2 I/O23r	F3 I/O24L	F4 Vss						^{F14} Vss	F15 I/O12R	F16 I/O11L	f17 Vddqf				
G1 I/O26L	^{G2} Vss	g3 I/O25L	G4 I/O24R		70V7519BF BF208 ⁽⁵⁾									g15 Vddql	G16 I/O10L	G17 I/O11F
h1 Vdd	h2 I/O26r	h3 Vddqr	h4 I/O25r											h15 IO9r	^{H16} Vss	н17 I/O10f
j1 Vddql	J2 Vdd	_{J3} Vss	_{J4} Vss											J15 Vdd	^{J16} Vss	j17 Vddqf
k1 I/O28R	к2 Vss	k3 I/O27r	^{K4} Vss			4	208-F Top	o Viev		N			k14 I/O7r	k15 Vddql	k16 I/O8r	к17 Vss
l1 I/O29R	l2 I/O28L	l3 Vddqr	l4 I/O27L										l14 I/O6r	l15 I/O7l	L16 Vss	l17 I/O8l
m1 Vddql	м2 I/O29L	m3 I/O30r	^{M4} Vss										M14 Vss	M15 I/O6L	^{M16} I/O5r	M17 Vddqf
N1 I/O31L	_{N2} Vss	n3 I/O31r	n4 I/O30l										n14 I/O3r	n15 Vddql	n16 I/O4r	N17 I/O5L
P1 I/O32R	p2 I/O32l	p3 Vddqr	P4 I/O35R	^{P5} TRST	^{P6} BA4r	P7 BAor	P8 A8R	P9 BE1R	P10 Vdd	P11 CLKr	P12 CNTENR	P13 A4R	P14 I/O2L	p15 I/O3l	P16 Vss	P17 I/O4L
R1 Vss	r2 I/O33l	r3 I/O34r	^{R4} TCK	r5 BA5r	r6 BA1r	r7 A9r	r8 BE2r	r9 CE0r	^{R10} Vss	^{R11} ADSR	R12 A5R	R13 A1R	^{R14} Vss	r15 Vddql	r16 I/O1r	r17 Vddqf
t1 I/O33r	t2 I/O34l	t3 Vddql	™ TMS	^{⊤5} NC	t6 BA2r	t7 A10r	t8 BE3r	^{T9} CE1R	^{T10} Vss	t11 R/Wr	t12 A6r	t13 A2r	^{T14} Vss	t15 I/Oor	^{T16} Vss	t17 I/O2r
U1 Vss	U2 I/O35l	u3 PL/FTR	U4 NC	U5 BA3R	U6 A11R	U7 A7R	U8 BE0R	U9 Vdd	U10 OER	U11 REPEA	U12 TrA3R	U13 Aor	U14 Vdd	U15 OPTr	U16 I/O0L	U17 I/O1L

Pin Configuration^(1,2,3,4)

5618 drw 02c

- 1. All VDD pins must be connected to 3.3V power supply.
- 2. All VDDQ pins must be connected to appropriate power supply: 3.3V if OPT pin for that port is set to VIH (3.3V), and 2.5V if OPT pin for that port is set to VIL (0V).
- 3. All Vss pins must be connected to ground supply.
- 4. Package body is approximately 15mm x 15mm x 1.4mm with 0.8mm ball pitch.
- 5. This package code is used to reference the package diagram.
- 6. This text does not indicate orientation of the actual part-marking.

Pin Configuration^(1,2,3,4) (con't.)

70V7519BC BC256⁽⁵⁾

256-Pin BGA Top View⁽⁶⁾

A1	^{A2}	A3	^{A4}	a5	A6	A7	A8	A9	A10	A11	A12	A13	A14	A15	A16
NC	TDI	NC	BA5L	BA2L	A11L	A8L	BE2L	CE1L	OEL	CNTENL	A5L	A2L	A0L	NC	NC
B1	^{B2}	^{B3}	^{B4}	^{B5}	B6	B7	B8	B9	^{B10}	B11	B12	B13	^{B14}	в15	^{B16} NC
I/O18L	NC	TDO	NC	BA3∟	BA0L	A9L	BE3L	CEOL	R/WL	REPEATL	A4L	A1L	Vdd	I/O17L	
C1	C2	C3	C4	C5	C6	C7	C8	C9	C10	C11	C12	C13	C14	C15	C16
I/O18R	I/O19L	Vss	BA4L	BA1L	A10L	A7L	BE1L	BE0L	CLKL	ADSL	A6L	A3L	OPT∟	I/O17R	I/O16L
D1	d2	d3	d4	d5	d6	d7	d8	d9	d10	d11	d12	d13	D14	D15	D16
I/O20R	I/O19R	I/O20L	PL/FTL	Vddql	Vddql	Vddqr	Vddqr	Vddql	Vddql	Vddqr	Vddqr	Vdd	I/O15R	I/O15L	I/O16R
e1	e2	e3	e4	e5	e6	e7	^{E8}	^{E9}	E10	e11	e12	e13	е14	e15	E16
I/O21r	I/O21l	I/O22L	Vddql	Vdd	Vdd	Vss	Vss	Vss	Vss	Vdd	Vdd	Vddqr	I/O13L	I/O14L	I/O14R
f1	F2	f3	f4	f5	F6	F7	F8	^{F9}	F10	F11	F12	f13	F14	F15	F16
I/O23l	I/O22R	I/O23r	Vddql	Vdd	Vss	Vss	Vss	Vss	Vss	Vss	Vdd	Vddqr	I/O12R	I/O13R	I/O12L
G1	G2	G3	g4	G5	G6	G7	_{G8}	^{G9}	G10	G11	G12	g13	G14	G15	G16
I/O24R	I/O24L	I/O25L	Vddqr	Vss	Vss	Vss	Vss	Vss	Vss	Vss	Vss	Vddql	I/O10L	I/O11L	I/O11R
н1	H2	H3	h4	H5	H6	H7	H8	H9	H10	H11	H12	h13	h14	H15	h16
I/O26L	I/O25R	I/O26R	Vddqr	Vss	Vss	Vss	Vss	Vss	Vss	Vss	Vss	Vddql	I/O9r	IO9∟	I/O10R
J1	j2	j3	j4	^{J5}	^{J6}	J7	_{J8}	^{J9}	J10	J11	J12	j13	J14	j15	J16
I/O27L	I/O28R	I/O27R	Vddql	Vss	Vss	Vss	Vss	Vss	Vss	Vss	Vss	Vddqr	I/O8R	I/O7r	I/O8L
k1	k2	k3	k4	K5	K6	к7	ка	к9	K10	к11	K12	k13	k14	к15	к16
I/O29R	I/O29L	I/O28l	Vddql	Vss	Vss	Vss	Vss	Vss	Vss	Vss	Vss	Vddqr	I/O6r	I/O6l	I/O7l
l1	l2	l3	l4	l5	L6	L7	L8	L9	L10	L11	l12	l13	l14	l15	l16
I/O30L	I/O31R	I/O30r	Vddqr	Vdd	Vss	Vss	Vss	Vss	Vss	Vss	Vdd	Vddql	I/O5l	I/O4r	I/O5r
m1	m2	M3	m4	^{M5}	M6	M7	^{M8}	^{M9}	M10	M11	M12	m13	m14	м15	M16
I/O32r	I/O32L	I/O31L	Vddqr	Vdd	Vdd	Vss	Vss	Vss	Vss	Vdd	Vdd	Vddql	I/O3r	І/Оз∟	I/O4L
n1	N2	n3	N4	n5	n6	n7	n8	n9	n10	n11	n12	N13	n14	n15	n16
I/O33l	I/O34R	I/O33r	PL/FTr	Vddqr	Vddqr	Vddql	Vddql	Vddqr	Vddqr	Vddql	Vddql	Vdd	I/O2l	I/O1r	I/O2r
P1	p2	^{РЗ}	P4	^{p5}	P6	P7	P8	P9	P10	^{p11}	P12	Р13	P14	p15	P16
I/O35R	I/O34L	TMS	BA4R	BA1r	A10R	A7R	BE1R	BE0R	CLKR	ADSr	A6R	Азк	I/Ool	I/Oor	I/O1L
r1	R2	^{R3}	^{R4}	r5	r6	r7	r8	r9	^{R10}	r11	R12	R13	^{R14}	R15	^{R16}
I/O35l	NC	TRST	NC	BA3r	BAor	A9r	BE3r	CEor	R/WR	REPEATR	A4R	A1R	OPTr	NC	NC
T1	T2	тз	t4	t5	t6	t7	t8	^{T9}	T10	t11	t12	t13	t14	^{T15}	T16
NC	TCK	NC	BA5r	BA2r	A11r	A8r	BE2r	CE1r	OEr	CNTENR	A5r	A2r	Aor	NC	NC

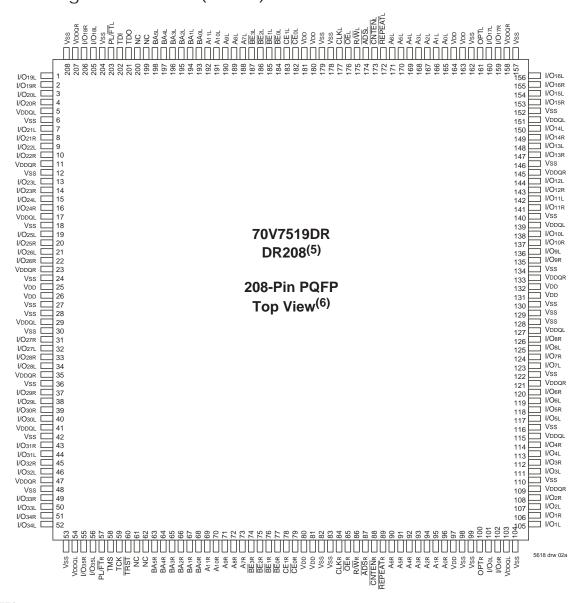
5618 drw 02d

NOTES:

1. All VDD pins must be connected to 3.3V power supply.

- 2. All VDDQ pins must be connected to appropriate power supply: 3.3V if OPT pin for that port is set to VIH (3.3V), and 2.5V if OPT pin for that port is set to VIL (0V).
- 3. All Vss pins must be connected to ground supply.
- 4. Package body is approximately 17mm x 17mm x 1.4mm, with 1.0mm ball-pitch.
- 5. This package code is used to reference the package diagram.
- 6. This text does not indicate orientation of the actual part-marking.

Pin Configuration^(1,2,3,4) (con't.)



- 1. All VDD pins must be connected to 3.3V power supply.
- 2. All VDDQ pins must be connected to appropriate power supply: 3.3V if OPT pin for that port is set to VIH (3.3V), and 2.5V if OPT pin for that port is set to VIL (0V).
- 3. All Vss pins must be connected to ground supply.
- 4. Package body is approximately 28mm x 28mm x 3.5mm.
- 5. This package code is used to reference the package diagram.
- 6. This text does not indicate orientation of the actual part-marking.

Pin Names

Left Port	Right Port	Names			
CEOL, CE1L	CEOR, CE1R	Chip Enables			
R/WL	R/ W r	Read/Write Enable			
ŌĒL	ŌĒr	Output Enable			
BAOL - BA5L	BAOR - BA5R	Bank Address ⁽⁴⁾			
Aol - A11l	Aor - A11r	Address			
1/Ool - 1/O35l	I/O0r - I/O35r	Data Input/Output			
CLKL	CLKR	Clock			
PL/FTL	PL/FTR	Pipeline/Flow-Through			
ADSL	ADS _R	Address Strobe Enable			
		Counter Enable			
REPEATL	REPEATR	Counter Repeat ⁽³⁾			
BEOL - BE3L	BEOR - BE3R	Byte Enables (9-bit bytes)			
VDDQL	VDDQR	Power (I/O Bus) (3.3V or 2.5V) ⁽¹⁾			
OPTL	OPTR	Option for selecting VDDQx ^(1,2)			
,	Vdd	Power (3.3V) ⁽¹⁾			
,	Vss	Ground (0V)			
	TDI	Test Data Input			
_	ГDO	Test Data Output			
-	ГСК	Test Logic Clock (10MHz)			
1	ſMS	Test Mode Select			
Ŧ	RST	Reset (Initialize TAP Controller)			

5618 tbl 01

- VDD, OPTx, and VDDox must be set to appropriate operating levels prior to applying inputs on the I/Os and controls for that port.
- 2. OPTx selects the operating voltage levels for the I/Os and controls on that port. If OPTx is set to VIH (3.3V), then that port's I/Os and controls will operate at 3.3V levels and VDDox must be supplied at 3.3V. If OPTx is set to VIL (0V), then that port's I/Os and address controls will operate at 2.5V levels and VDDox must be supplied at 2.5V. The OPT pins are independent of one another—both ports can operate at 3.3V levels, both can operate at 2.5V levels, or either can operate at 3.3V with the other at 2.5V.
- When REPEAT x is asserted, the counter will reset to the last valid address loaded via ADS x.
- 4. Accesses by the ports into specific banks are controlled by the bank address pins under the user's direct control: each port can access any bank of memory with the shared array that is not currently being accessed by the opposite port (i.e., BA0L BA5L ≠ BA0R BA5R). In the event that both ports try to access the same bank at the same time, neither access will be valid, and data at the two specific addresses targeted by the ports within that bank may be corrupted (in the case that either or both ports are writing) or may result in invalid output (in the case that both ports are trying to read).

Tru	th T	abl	e I–	-Re	ad/\	Nrit	e ai	nd E	Inable	e Cont	rol ^{(1,2}	,3,4)	
	CLK	Ē₽	CE1	BE 3	BE 2	BE 1	ĒĒ₀	R/W	Byte 3 I/O27-35	Byte 2 I/O18-26	Byte 1 I/O9-17	Byte 0 I/Oo-8	MODE
Х	Ŷ	Н	Х	Х	Х	Х	Х	Х	High-Z	High-Z	High-Z	High-Z	Deselected–Power Down
Х	\uparrow	Х	L	Х	Х	Х	Х	Х	High-Z	High-Z	High-Z	High-Z	Deselected–Power Down
Х	\uparrow	L	Н	Н	Н	Н	Н	Х	High-Z	High-Z	High-Z	High-Z	All Bytes Deselected
Х	Ŷ	L	Н	Н	Н	Н	L	L	High-Z	High-Z	High-Z	Diℕ	Write to Byte 0 Only
Х	\uparrow	L	Н	Н	Н	L	Н	L	High-Z	High-Z	Din	High-Z	Write to Byte 1 Only
Х	\uparrow	L	Н	Н	L	Н	Н	L	High-Z	Din	High-Z	High-Z	Write to Byte 2 Only
Х	\uparrow	L	Н	L	Н	Н	Н	L	Din	High-Z	High-Z	High-Z	Write to Byte 3 Only
Х	\uparrow	L	Н	Н	Н	L	L	L	High-Z	High-Z	Din	Din	Write to Lower 2 Bytes Only
Х	\uparrow	L	Н	L	L	Н	Н	L	Din	Din	High-Z	High-Z	Write to Upper 2 bytes Only
Х	\uparrow	L	Н	L	L	L	L	L	Din	Din	Din	Din	Write to All Bytes
L	\uparrow	L	Н	Н	Н	Н	L	Н	High-Z	High-Z	High-Z	Dout	Read Byte 0 Only
L	\uparrow	L	Н	Н	Н	L	Н	Н	High-Z	High-Z	Dout	High-Z	Read Byte 1 Only
L	Ŷ	L	Н	Н	L	Н	Н	Н	High-Z	Dout	High-Z	High-Z	Read Byte 2 Only
L	\uparrow	L	Н	L	Н	Н	Н	Н	Dout	High-Z	High-Z	High-Z	Read Byte 3 Only
L	\uparrow	L	Н	Н	Н	L	L	Н	High-Z	High-Z	Dout	Dout	Read Lower 2 Bytes Only
L	\uparrow	L	Н	L	L	Н	Н	Н	Dout	Dout	High-Z	High-Z	Read Upper 2 Bytes Only
L	\uparrow	L	Н	L	L	L	L	Н	Dout	Dout	Dout	Dout	Read All Bytes
Н	Х	Х	Х	Х	Х	Х	Х	Х	High-Z	High-Z	High-Z	High-Z	Outputs Disabled

NOTES:

IDT70V7519S

1. "H" = VIH, "L" = VIL, "X" = Don't Care.

2. ADS, CNTEN, REPEAT are set as appropriate for address access. Refer to Truth Table II for details.

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3. OE is an asynchronous input signal.

4. It is possible to read or write any combination of bytes during a given access. A few representative samples have been illustrated here.

Truth Table II—Address and Address Counter Control^(1,2,7)

Address	Previous Address	Addr Used	CLK		CNTEN	REPEAT ⁽⁶⁾	I/O ⁽³⁾	MODE
An	Х	An	\uparrow	L ⁽⁴⁾	Х	Н	Dvo (n)	External Address Used
Х	An	An + 1	\uparrow	Н	L ⁽⁵⁾	Н	D⊮o(n+1)	Counter Enabled—Internal Address generation
Х	An + 1	An + 1	\uparrow	Н	Н	Н	D⊮o(n+1)	External Address Blocked—Counter disabled (An + 1 reused)
Х	Х	An	\uparrow	Х	Х	L ⁽⁴⁾	Di/o (0)	Counter Set to last valid ADS load

NOTES:

1. "H" = VIH, "L" = VIL, "X" = Don't Care.

2. Read and write operations are controlled by the appropriate setting of R/\overline{W} , \overline{CE}_0 , CE₁, \overline{BE}_n and \overline{OE} .

3. Outputs configured in flow-through output mode: if outputs are in pipelined mode the data out will be delayed by one cycle.

4. ADS and REPEAT are independent of all other memory control signals including CEo, CE1 and BEn

5. The address counter advances if CNTEN = VIL on the rising edge of CLK, regardless of all other memory control signals including CE0, CE1, BEn.

6. When REPEAT is asserted, the counter will reset to the last valid address loaded via ADS. This value is not set at power-up: a known location should be loaded via ADS during initialization if desired. Any subsequent ADS access during operations will update the REPEAT address location.

7. The counter includes bank address and internal address. The counter will advance across bank boundaries. For example, if the counter is in Bank 0, at address FFFh, and is advanced one location, it will move to address 0h in Bank 1. By the same token, the counter at FFFh in Bank 63 will advance to 0h in Bank 0. Refer to Timing Waveform of Counter Repeat, page 18. Care should be taken during operation to avoid having both counters point to the same bank (i.e., ensure BAoL - BA5L ≠ BA0R - BA5R), as this condition will invalidate the access for both ports. Please refer to the functional description on page 19 for details.

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5618 tbl 02

5618 tbl 03

Industrial and Commercial Temperature Ranges

High-Speed 256K x 36 Synchronous Bank-Switchable Dual-Port Static RAM

Industrial and Commercial Temperature Ranges

5618 tbl 05a

5618 tbl 05b

Recommended Operating Temperature and Supply Voltage⁽¹⁾

Grade	Ambient Temperature	GND	Vdd
Commercial	0°C to +70°C	0V	3.3V <u>+</u> 150mV
Industrial	-40°C to +85°C	0V	3.3V <u>+</u> 150mV

NOTE:

1. This is the parameter TA. This is the "instant on" case temperature.

Absolute Maximum Ratings⁽¹⁾

Symbol	Rating	Commercial & Industrial	Unit						
Vterm ⁽²⁾	Terminal Voltage with Respect to GND	-0.5 to +4.6	V						
Tbias	Temperature Under Bias	-55 to +125	٥C						
Tstg	Storage Temperature	-65 to +150	٥C						
Ιουτ	DC Output Current	50	mA						
5618 tbl 0									

NOTES:

 Stresses greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

2. VTERM must not exceed VDD + 150mV for more than 25% of the cycle time or 4ns maximum, and is limited to \leq 20mA for the period of VTERM \geq VDD + 150mV.

Recommended DC Operating Conditions with VDDQ at 2.5V

Symbol	Parameter	Min.	Тур.	Max.	Unit
Vdd	Core Supply Voltage	3.15	3.3	3.45	V
VDDQ I/O Supply Voltage ⁽³⁾		2.4	2.5	2.6	V
Vss	Vss Ground		0	0	V
Vih	Input High Voltage (Address & Control Inputs)	1.7		Vddq + 100mV ⁽²⁾	V
V⊮	Vн Input High Voltage - I/O ⁽³⁾			$V_{DDQ} + 100 mV^{(2)}$	V
Vil	Input Low Voltage			0.7	V

NOTES:

5618 tbl 04

1. Undershoot of VIL $_{\geq}$ -1.5V for pulse width less than 10ns is allowed.

2. VTERM must not exceed VDDQ + 100mV.

 To select operation at 2.5V levels on the I/Os and controls of a given port, the OPT pin for that port must be set to VIL (0V), and VDDox for that port must be supplied as indicated above.

Symbol	Parameter	Min.	Тур.	Мах.	Unit
Vdd	Core Supply Voltage	3.15	3.3	3.45	V
VDDQ	I/O Supply Voltage ⁽³⁾	3.15	3.3	3.45	V
Vss	Ground	0	0	0	V
V⊮	Input High Voltage (Address & Control Inputs) ⁽³⁾	2.0		Vddq + 150mV ⁽²⁾	V
V⊪	Input High Voltage - I/O ⁽³⁾	2.0	—	$V_{DDQ} + 150 mV^{(2)}$	V
VIL	Input Low Voltage	-0.3(1)		0.8	V

Recommended DC Operating Conditions with VDDQ at 3.3V

NOTES:

1. Undershoot of VIL \geq -1.5V for pulse width less than 10ns is allowed.

2. VTERM must not exceed VDDQ + 150mV.

3. To select operation at 3.3V levels on the I/Os and controls of a given port, the OPT pin for that port must be set to VIH (3.3V), and VDDOX for that port must be supplied as indicated above.

High-Speed 256K x 36 Synchronous Bank-Switchable Dual-Port Static RAM

Industrial and Commercial Temperature Ranges

5618 tbl 08

Capacitance⁽¹⁾

Symbol	Parameter	Conditions ⁽²⁾	Мах.	Unit
Cin	Input Capacitance	VIN = 3dV	8	pF
Cout ⁽³⁾	Output Capacitance	Vout = 3dV	10.5	pF
				5618 tbl 07

NOTES:

1. These parameters are determined by device characterization, but are not production tested.

2. 3dV references the interpolated capacitance when the input and output switch from 0V to 3V or from 3V to 0V.

3. COUT also references CI/O.

DC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range (VDD = $3.3V \pm 150$ mV)

			70V7	70V7519S	
Symbol	Parameter	Test Conditions	Min.	Max.	Unit
lu	Input Leakage Current ⁽¹⁾	$V_{DDQ} = Max., V_{IN} = 0V$ to V_{DDQ}		10	μA
Ilo	Output Leakage Current ⁽¹⁾	\overline{CE}_{0} = Vih or CE1 = Vil, Vout = 0V to VDDQ		10	μA
Vol (3.3V)	Output Low Voltage ⁽²⁾	IOL = +4mA, $VDDQ = Min$.		0.4	V
Voн (3.3V)	Output High Voltage ⁽²⁾	Ioh = -4mA, VDDQ = Min.	2.4	_	V
Vol (2.5V)	Output Low Voltage ⁽²⁾	IOL = +2mA, $VDDQ = Min$.		0.4	V
Voн (2.5V)	Output High Voltage ⁽²⁾	IOH = -2mA, VDDQ = Min.	2.0	_	V

NOTES:

1. At VDD \leq 2.0V leakages are undefined.

2. VDDQ is selectable (3.3V/2.5V) via OPT pins. Refer to p.5 for details.

Industrial and Commercial Temperature Ranges

DC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range⁽⁵⁾ ($V_{DD} = 3.3V \pm 150 \text{mV}$)

						9S200 ⁽⁷⁾ I Only	Co	9S166 ⁽⁶⁾ m'l Ind	Co	19S133 m'l Ind	
Symbol	Parameter	Test Condition	Versio	n	Тур. ⁽⁴⁾	Мах.	Typ. ⁽⁴⁾	Мах.	Typ. ⁽⁴⁾	Max.	Unit
IDD	Dynamic Operating	CEL and CER= VIL,	COM'L	S	815	950	675	790	550	645	mA
	Current (Both Ports Active)		IND	S		_	675	830	550	675	
ISB1		$\overline{CEL} = \overline{CER} = VIH$ f = fMAX ⁽¹⁾	COM'L	S	340	410	275	340	250	295	mA
			IND	S			275	355	250	310	
ISB2	(One Port - TTL A	\overline{CE} "A" = VIL and \overline{CE} "B" = VIH ⁽³⁾	COM'L	DM'L S 690 770 515 640	460	520	mA				
		Active Port Outputs Disabled, f=fMAX ⁽¹⁾	IND	S		-	515	660	460	545	
ISB3	(Both Ports - CMOS VIN >	Both Ports $\overline{CE}L$ and $\overline{CE}R \ge VDDQ - 0.2V$,	COM'L	S	10	10 30 10 30 10	10	30	mA		
		$ \begin{array}{l} \mbox{Vin} \geq \mbox{VdDQ} \ \text{-} \ 0.2 \mbox{Vin} \leq \mbox{0.2V}, \\ \mbox{f} = \mbox{0}^{(2)} \end{array} $	IND	S			10	40	10	40	
	$\label{eq:constraint} \begin{array}{llllllllllllllllllllllllllllllllllll$, <u> </u>	COM'L	S	690	770	515	640	460	520	mA
			IND	S		_	515	660	460	545	
	•	•	•						•	56	618 tbl 09

NOTES:

1. At f = fmax, address and control lines (except Output Enable) are cycling at the maximum frequency clock cycle of 1/tcyc, using "AC TEST CONDITIONS" at input levels of GND to 3V.

- 2. f = 0 means no address, clock, or control lines change. Applies only to input at CMOS level standby.
- 3. Port "A" may be either left or right port. Port "B" is the opposite from port "A".
- 4. <u>VDD</u> = 3.3V, TA = 25° C for Typ, and are not production tested. IDD DC(f=0) = 120mA (Typ).
- 5. $\overline{CE}x = VIL$ means $\overline{CE}ox = VIL$ and CE1x = VIH
- $\overline{CE}x = VIH$ means $\overline{CE}ox = VIH$ or CE1x = VIL
- $\overline{CE}x \leq$ 0.2V means $\overline{CE}\textsc{ox} \leq$ 0.2V and CE1x \geq VDDQ 0.2V
- $\overline{\text{CE}}\text{x} \geq \text{V}\text{DDQ}$ 0.2V means $\overline{\text{CE}}\text{ox} \geq \text{V}\text{DDQ}$ 0.2V or CE1x $\leq 0.2\text{V}$
- "X" represents "L" for left port or "R" for right port.
- 6. 166MHz Industrial Temperature not available in BF208 package.
- 7. This speed grade available when VDD0 = 3.3.V for a specific port (i.e., OPTx = ViH). This speed grade available in BC-256 package only.

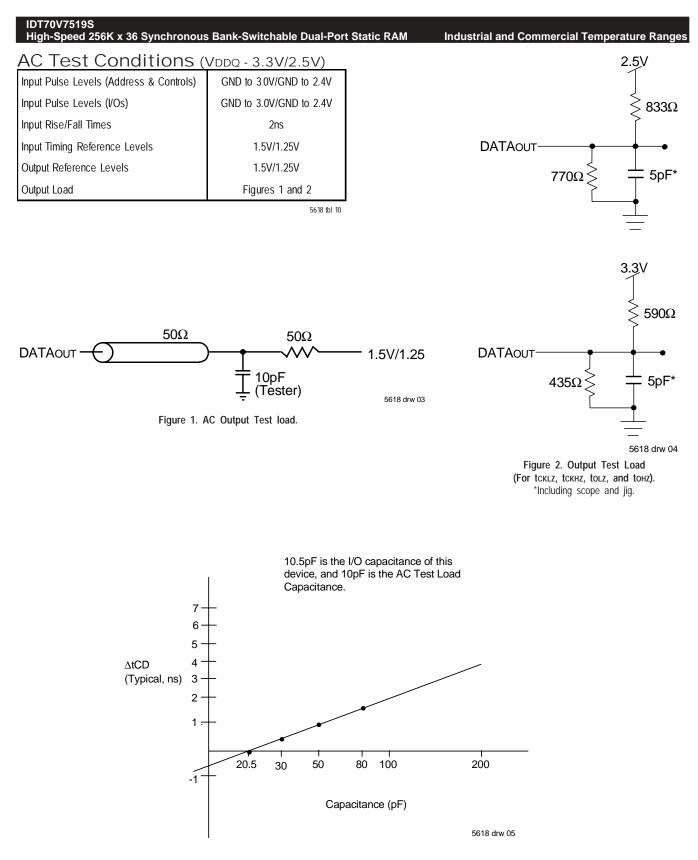


Figure 3. Typical Output Derating (Lumped Capacitive Load).

AC Electrical Characteristics Over the Operating Temperature Range (Read and Write Cycle Timing)^(2,3) (VDD = $3.3V \pm 150mV$, TA = 0°C to +70°C)

	Parameter		70V7519S200 ⁽⁵⁾ Com'l Only		70V7519S166 ^(3,4) Com'l & Ind		70V7519S133 ⁽³⁾ Com'l & Ind	
Symbol			Max.	Min.	Max.	Min.	Max.	Unit
tcyc1	Clock Cycle Time (Flow-Through) ⁽¹⁾	15	—	20	_	25		ns
tcyc2	Clock Cycle Time (Pipelined) ⁽¹⁾	5	—	6	_	7.5		ns
tCH1	Clock High Time (Flow-Through) ⁽¹⁾	5	—	6	—	7		ns
tCL1	Clock Low Time (Flow-Through) ⁽¹⁾	5	—	6	_	7		ns
tCH2	Clock High Time (Pipelined) ⁽²⁾	2.0	—	2.1	_	2.6		ns
tCL2	Clock Low Time (Pipelined) ⁽¹⁾	2.0	—	2.1	_	2.6		ns
tR	Clock Rise Time		1.5		1.5		1.5	ns
tF	Clock Fall Time		1.5		1.5		1.5	ns
tsa	Address Setup Time	1.5	—	1.7	—	1.8	_	ns
tha	Address Hold Time	0.5	_	0.5	_	0.5	_	ns
tsc	Chip Enable Setup Time	1.5	_	1.7	_	1.8	_	ns
thc	Chip Enable Hold Time	0.5	—	0.5	_	0.5	_	ns
tsв	Byte Enable Setup Time	1.5	—	1.7	_	1.8		ns
tнв	Byte Enable Hold Time	0.5	—	0.5	_	0.5		ns
tsw	R/W Setup Time	1.5	—	1.7	_	1.8		ns
tHW	R/W Hold Time	0.5	—	0.5	_	0.5		ns
tsp	Input Data Setup Time	1.5	_	1.7	-	1.8	_	ns
thd	Input Data Hold Time	0.5	_	0.5	-	0.5	_	ns
tsad	ADS Setup Time	1.5	—	1.7	_	1.8		ns
thad	ADS Hold Time		_	0.5	_	0.5		ns
tscn	CNTEN Setup Time	1.5	_	1.7	_	1.8		ns
then	CNTEN Hold Time	0.5	_	0.5	_	0.5		ns
t SRPT	REPEAT Setup Time	1.5	_	1.7	_	1.8	_	ns
t HRPT	REPEAT Hold Time	0.5	_	0.5	_	0.5	_	ns
toe	Output Enable to Data Valid		4.0		4.0		4.2	ns
tolz	Output Enable to Output Low-Z	0.5	_	0.5	_	0.5	_	ns
tонz	Output Enable to Output High-Z	1	3.4	1	3.6	1	4.2	ns
tCD1	Clock to Data Valid (Flow-Through) ⁽¹⁾		10		12	_	15	ns
tCD2	Clock to Data Valid (Pipelined) ⁽¹⁾	—	3.4	_	3.6	_	4.2	ns
tDC	Data Output Hold After Clock High	1	—	1	_	1	_	ns
tскнz	Clock High to Output High-Z	1	3.4	1	3.6	1	4.2	ns
tcklz.	Clock High to Output Low-Z	0.5	_	0.5	_	0.5	_	ns
Port-to-Port	- Delay	·	-		-			
tco	Clock-to-Clock Offset	5.0	_	6.0	_	7.5	_	ns

2. All input signals are synchronous with respect to the clock except for the asynchronous Output Enable (OE) and FT/PIPE. FT/PIPE should be treated as a DC signal, i.e. steady state during operation.

3. These values are valid for either level of VDDQ (3.3V/2.5V). See page 5 for details on selecting the desired operating voltage levels for each port.

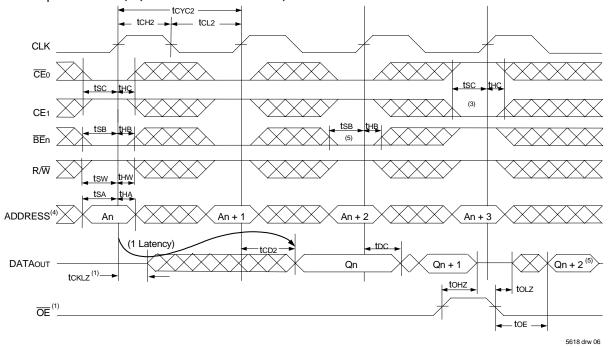
4. 166MHz Industrial Temperature not available in BF208 package.

5. This speed grade available when VDDQ = 3.3.V for a specific port (i.e., OPTx = VIH). This speed grade available in BC256 package only.

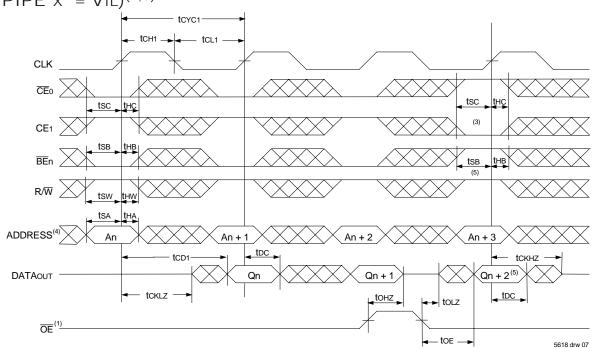
^{1.} The Pipelined output parameters (tcvc2, tcb2) apply to either or both left and right ports when \overline{FT} /PIPEx = VIH. Flow-through parameters (tcvc1, tcb1) apply when \overline{FT} /PIPEx = VIL for that port.

Industrial and Commercial Temperature Ranges

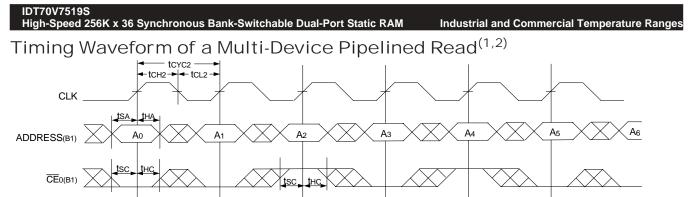
Timing Waveform of Read Cycle for Pipelined Operation (**ADS** Operation) (**FT**/PIPE'x' = VIH)⁽²⁾

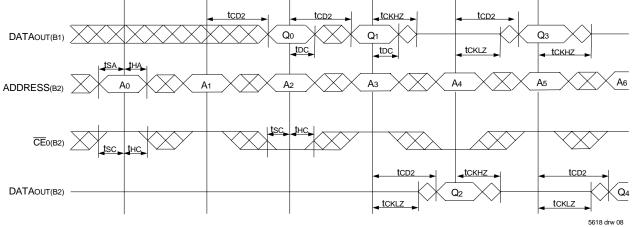




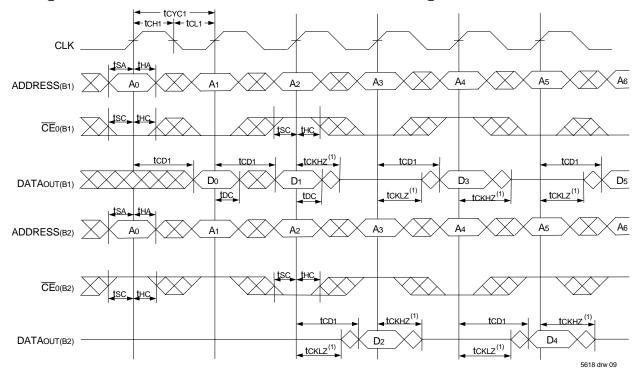


- 1. DE is asynchronously controlled; all other inputs are synchronous to the rising clock edge.
- 2. $\overline{\text{ADS}} = \text{VIL}, \overline{\text{CNTEN}} \text{ and } \overline{\text{REPEAT}} = \text{VIH}.$
- 3. The output is disabled (High-Impedance state) by $\overline{CE}_0 = V_{IH}$, $CE_1 = V_{IL}$, $\overline{BE}_n = V_{IH}$ following the next rising edge of the clock. Refer to Truth Table 1.
- 4. Addresses do not have to be accessed sequentially since ADS = VIL constantly loads the address on the rising edge of the CLK; numbers are for reference use only.
- 5. If BEn was HIGH, then the appropriate Byte of DATAOUT for Qn + 2 would be disabled (High-Impedance state).
- 6. "x" denotes Left or Right port. The diagram is with respect to that port.





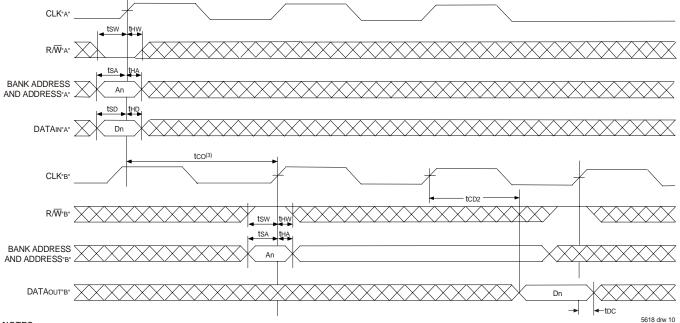
Timing Waveform of a Multi-Device Flow-Through Read^(1,2)



- 1. B1 Represents Device #1; B2 Represents Device #2. Each Device consists of one IDT70V7519 for this waveform,
- and are setup for depth expansion in this example. ADDRESS(B1) = ADDRESS(B2) in this situation.
- 2. $\overline{\text{BE}}n$, $\overline{\text{OE}}$, and $\overline{\text{ADS}}$ = VIL; $\overline{\text{CE1(B1)}}$, $\overline{\text{CE1(B2)}}$, $\overline{\text{R/W}}$, $\overline{\text{CNTEN}}$, and $\overline{\overline{\text{REPEAT}}}$ = VIH.

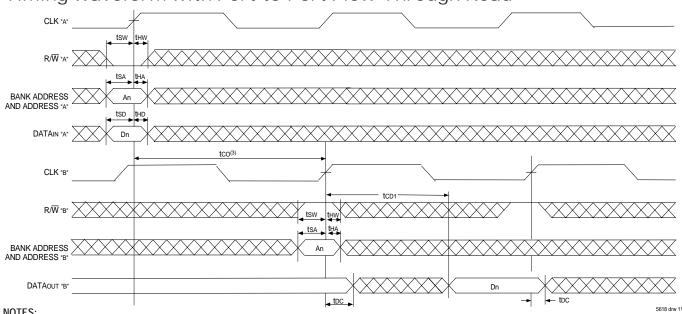
Industrial and Commercial Temperature Ranges

Timing Waveform of Port A Write to Pipelined Port B Read^(1,2,4)



NOTES:

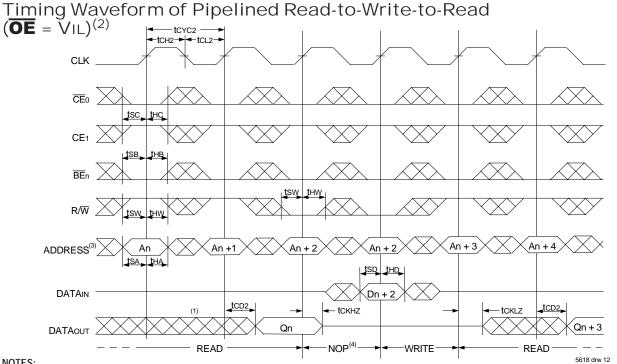
- \overline{CE}_0 , \overline{BE}_n , and $\overline{ADS} = V_{IL}$; CE1, \overline{CNTEN} , and $\overline{REPEAT} = V_{IH}$. 1.
- 2. $\overline{OE} = V_{IL}$ for Port "B", which is being read from. $\overline{OE} = V_{IH}$ for Port "A", which is being written to.
- 3. If tco < minimum specified, then operations from both ports are INVALID. If tco ≥ minimum, then data from Port "B" read is available on first Port "B" clock cycle (ie, time from write to valid read on opposite port will be tco + tcyc2 + tcp2).
- 4. All timing is the same for Left and Right ports. Port "A" may be either Left or Right port. Port "B" is the opposite of Port "A"



Timing Waveform with Port-to-Port Flow-Through Read^(1,2,4)

- 1. \overline{CE}_{0} , \overline{BE}_{n} , and $\overline{ADS} = V_{IL}$; CE_{1} , \overline{CNTEN} , and $\overline{REPEAT} = V_{IH}$.
- 2. \overline{OE} = VIL for the Right Port, which is being read from. \overline{OE} = VIH for the Left Port, which is being written to.
- 3. If tco < minimum specified, then operations from both ports are INVALID. If tco ≥ minimum, then data from Port "B" read is available on first Port "B" clock cycle (i.e., time from write to valid read on opposite port will be tco + tco1).
- 4. All timing is the same for both left and right ports. Port "A" may be either left or right port. Port "B" is the opposite of Port "A".

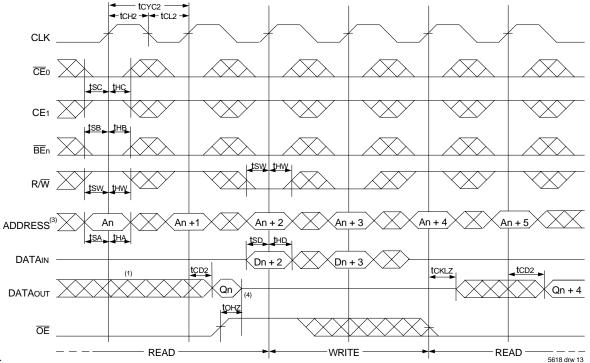
Industrial and Commercial Temperature Ranges



NOTES:

- 1. Output state (High, Low, or High-impedance) is determined by the previous cycle control signals.
- CEo, BEn, and ADS = VIL; CE1, CNTEN, and REPEAT = VIH. "NOP" is "No Operation". 2.
- 3. Addresses do not have to be accessed sequentially since ADS = VIL constantly loads the address on the rising edge of the CLK; numbers are for reference use only.
- 4. "NOP" is "No Operation." Data in memory at the selected address may be corrupted and should be re-written to guarantee data integrity.

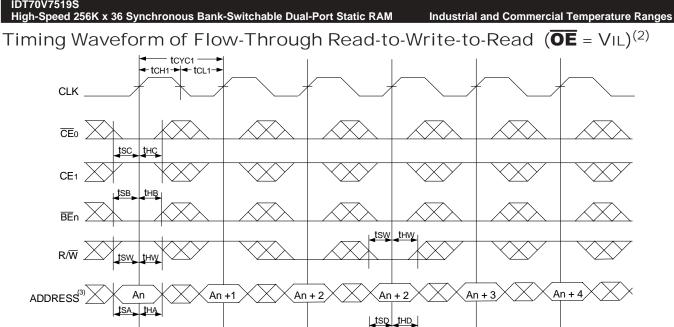
Timing Waveform of Pipelined Read-to-Write-to-Read (OE Controlled)⁽²⁾

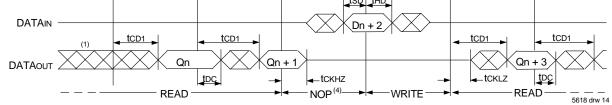


NOTES:

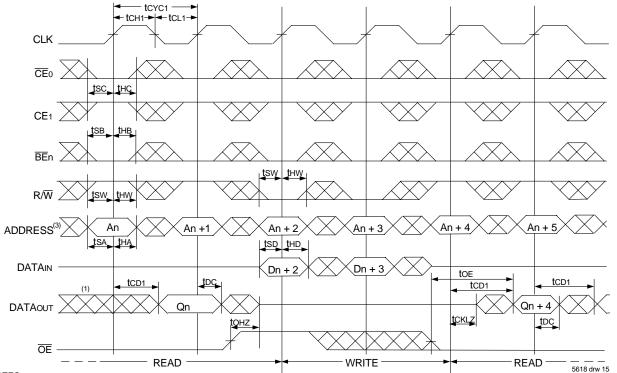
- 1. Output state (High, Low, or High-impedance) is determined by the previous cycle control signals.
- CEO, BEn, and ADS = VIL; CE1, CNTEN, and REPEAT = VIH. 2.
- 3. Addresses do not have to be accessed sequentially since ADS = VIL constantly loads the address on the rising edge of the CLK; numbers are for reference use only.

This timing does not meet requirements for fastest speed grade. This waveform indicates how logically it could be done if timing so allows. 4





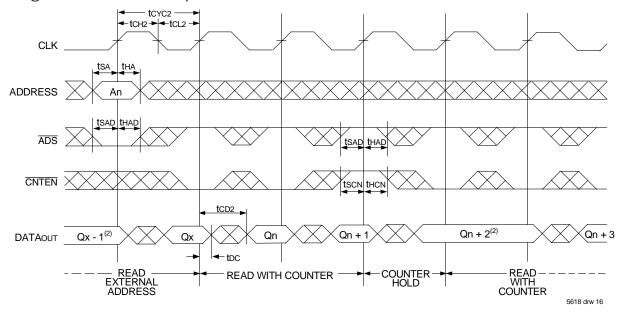
Timing Waveform of Flow-Through Read-to-Write-to-Read (OE Controlled)⁽²⁾



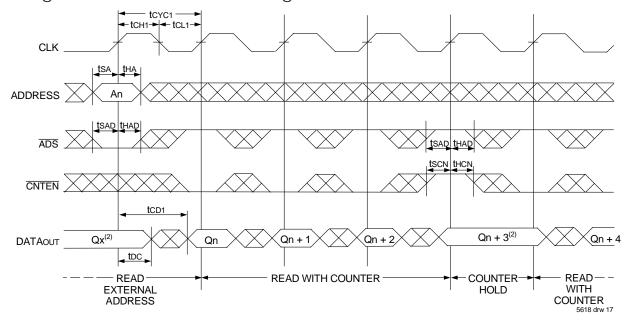
- 1. Output state (High, Low, or High-impedance) is determined by the previous cycle control signals.
- 2. \overline{CE}_0 , \overline{BE}_n , and $\overline{ADS} = VIL$; CE_1 , \overline{CNTEN} , and $\overline{REPEAT} = VIH$.
- 3. Addresses do not have to be accessed sequentially since ADS = VIL constantly loads the address on the rising edge of the CLK; numbers are for reference use only.
- 4. "NOP" is "No Operation." Data in memory at the selected address may be corrupted and should be re-written to guarantee data integrity.

Industrial and Commercial Temperature Ranges

Timing Waveform of Pipelined Read with Address Counter Advance⁽¹⁾



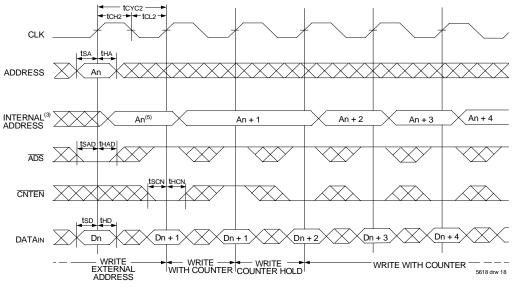
Timing Waveform of Flow-Through Read with Address Counter Advance⁽¹⁾



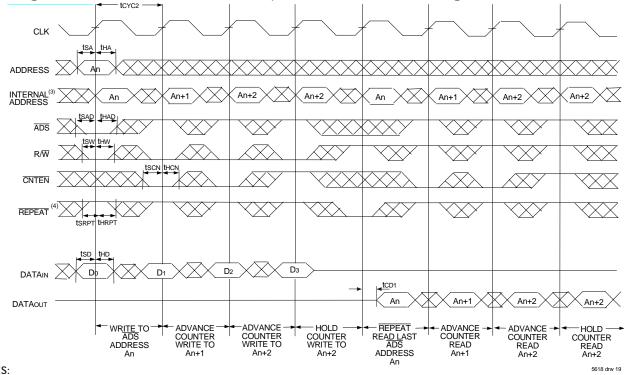
- 1. \overline{CE}_{0} , \overline{OE} , $\overline{BEn} = VIL$; CE1, R/W, and $\overline{REPEAT} = VIH$.
- 2. If there is no address change via $\overline{ADS} = V_{IL}$ (loading a new address) or $\overline{CNTEN} = V_{IL}$ (advancing the address), i.e. $\overline{ADS} = V_{IH}$ and $\overline{CNTEN} = V_{IH}$, then the data output remains constant for subsequent clocks.

Industrial and Commercial Temperature Ranges

Timing Waveform of Write with Address Counter Advance (Flow-through or Pipelined Inputs)^(1,6)



Timing Waveform of Counter Repeat for Flow Through Mode^(2,6,7)



- 1. \overline{CE}_{0} , \overline{BE}_{n} , and $R/\overline{W} = V_{IL}$; CE1 and $\overline{REPEAT} = V_{IH}$.
- 2. \overline{CE} 0, \overline{BE} n = VIL; CE1 = VIH.
- 3. The "Internal Address" is equal to the "External Address" when \overline{ADS} = VIL and equals the counter output when \overline{ADS} = VIH.
- 4. No dead cycle exists during REPEAT operation. A READ or WRITE cycle may be coincidental with the counter REPEAT cycle: Address loaded by last valid ADS load will be accessed. For more information on REPEAT function refer to Truth Table II.
- 5. CNTEN = VIL advances Internal Address from 'An' to 'An +1'. The transition shown indicates the time required for the counter to advance. The 'An +1'Address is written to during this cycle.
- 6. The counter includes bank address and internal address. The counter will advance across bank boundaries. For example, if the counter is in Bank 0, at address FFFh, and is advanced one location, it will move to address 0h in Bank 1. By the same token, the counter at FFFh in Bank 63 will advance to 0h in Bank 0.
- 7. For Pipelined Mode user should add 1 cycle latency for outputs as per timing waveform of read cycle for pipelined operations.

High-Speed 256K x 36 Synchronous Bank-Switchable Dual-Port Static RAM

Functional Description

The IDT70V7519 is a high-speed 256Kx36 (9 Mbit) synchronous Bank-Switchable Dual-Ported SRAM organized into 64 independent 4Kx36 banks. Based on a standard SRAM core instead of a traditional true dual-port memory core, this bank-switchable device offers the benefits of increased density and lower cost-per-bit while retaining many of the features of true dual-ports. These features include simultaneous, random access to the shared array, separate clocks per port, 166 MHz operating speed, full-boundary counters, and pinouts compatible with the IDT70V3599 (128Kx36) dual-port family.

The two ports are permitted independent, simultaneous access into separate banks within the shared array. Access by the ports into specific banks are controlled by the bank address pins under the user's direct control: each port can access any bank of memory with the shared array that is not currently being accessed by the opposite port (i.e., BAOL - BA5L \neq BAOR - BA5R). In the event that both ports try to access the same bank at the same time, neither access will be valid, and data at the two specific addresses targeted by the ports within that bank may be corrupted (in the case that either or both ports are writing) or may result in invalid output (in the case that both ports are trying to read).

The IDT70V7519 provides a true synchronous Dual-Port Static RAM

interface. Registered inputs provide minimal setup and hold times on address, data and all critical control inputs.

Industrial and Commercial Temperature Ranges

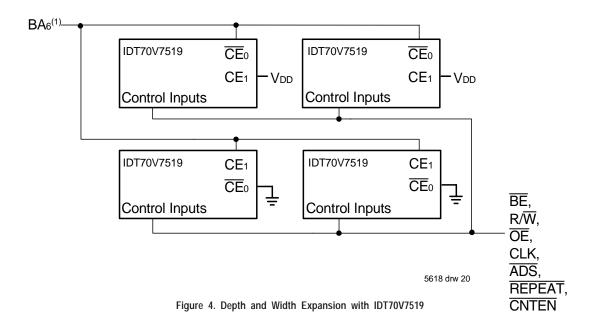
An asynchronous output enable is provided to ease asynchronous bus interfacing. Counter enable inputs are also provided to stall the operation of the address counters for fast interleaved memory applications.

A HIGH on CEo or a LOW on CE1 for one clock cycle will power down the internal circuitry on each port (individually controlled) to reduce static power consumption. Dual chip enables allow easier banking of multiple IDT70V7519s for depth expansion configurations. Two cycles are required with CE0 LOW and CE1 HIGH to read valid data on the outputs.

Depth and Width Expansion

The IDT70V7519 features dual chip enables (refer to Truth Table I) in order to facilitate rapid and simple depth expansion with no requirements for external logic. Figure 4 illustrates how to control the various chip enables in order to expand two devices in depth.

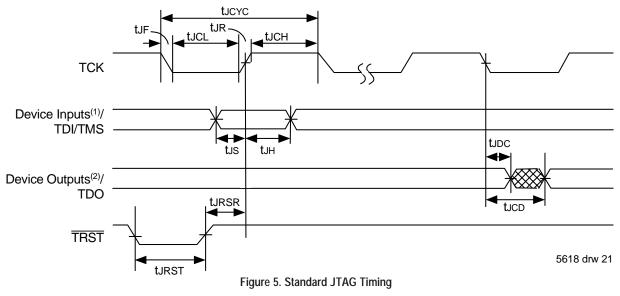
The IDT70V7519 can also be used in applications requiring expanded width, as indicated in Figure 4. Through combining the control signals, the devices can be grouped as necessary to accommodate applications needing 72-bits or wider.



NOTE:

1. In the case of depth expansion, the additional address pin logically serves as an extension of the bank address. Accesses by the ports into specific banks are controlled by the bank address pins under the user's direct control: each port can access any bank of memory within the shared array that is not currently being accessed by the opposite port (i.e., BAoL - BAoL ≠ BAoR - BAoR). In the event that both ports try to access the same bank at the same time, neither access will be valid, and data at the two specific addresses targeted by the parts within that bank may be corrupted (in the case that either or both parts are writing) or may result in invalid output (in the case that both ports are trying to read).

JTAG Timing Specifications



NOTES:

1. Device inputs = All device inputs except TDI, TMS, TRST, and TCK.

2. Device outputs = All device outputs except TDO.

		70V7519		
Symbol	Parameter	Min.	Мах.	Units
ticyc	JTAG Clock Input Period	100		ns
рсн	JTAG Clock HIGH	40		ns
tJCL	JTAG Clock Low	40	_	ns
UR	JTAG Clock Rise Time		3(1)	ns
UF	JTAG Clock Fall Time		3(1)	ns
U RST	JTAG Reset	50		ns
tursr	JTAG Reset Recovery	50	_	ns
ticd	JTAG Data Output		25	ns
tudc	JTAG Data Output Hold	0		ns
tıs	JTAG Setup	15		ns
tн	JTAG Hold	15		ns

JTAG AC Electrical Characteristics^(1,2,3,4)

NOTES:

1. Guaranteed by design.

2. 30pF loading on external output signals.

3. Refer to AC Electrical Test Conditions stated earlier in this document.

4. JTAG operations occur at one speed (10MHz). The base device may run at any speed specified in this datasheet.

5618 tbl 12

Identification Register Definitions

Instruction Field	Value	Description
Revision Number (31:28)	0x0	Reserved for version number
IDT Device ID (27:12)	0x300	Defines IDT part number
IDT JEDEC ID (11:1)	0x33	Allows unique identification of device vendor as IDT
ID Register Indicator Bit (Bit 0)	1	Indicates the presence of an ID register

5618 tbl 13

5618 tbl 15

Scan Register Sizes

Register Name	Bit Size
Instruction (IR)	4
Bypass (BYR)	1
Identification (IDR)	32
Boundary Scan (BSR)	Note (3)

5618 tbl 14

System Interface Parameters

Instruction	Code	Description
EXTEST	0000	Forces contents of the boundary scan cells onto the device outputs ⁽¹⁾ . Places the boundary scan register (BSR) between TDI and TDO.
BYPASS	1111	Places the bypass register (BYR) between TDI and TDO.
IDCODE	0010	Loads the ID register (IDR) with the vendor ID code and places the register between TDI and TDO.
HIGHZ	0100	Places the bypass register (BYR) between TDI and TDO. Forces all device output drivers to a High-Z state.
CLAMP	0011	Uses BYR. Forces contents of the boundary scan cells onto the device outputs. Places the bypass register (BYR) between TDI and TDO.
SAMPLE/PRELOAD	0001	Places the boundary scan register (BSR) between TDI and TDO. SAMPLE allows data from device inputs ⁽²⁾ and outputs ⁽¹⁾ to be captured in the boundary scan cells and shifted serially through TDO. PRELOAD allows data to be input serially into the boundary scan cells via the TDI.
RESERVED	All other codes	Several combinations are reserved. Do not use codes other than those identified above.

NOTES:

1. Device outputs = All device outputs except TDO.

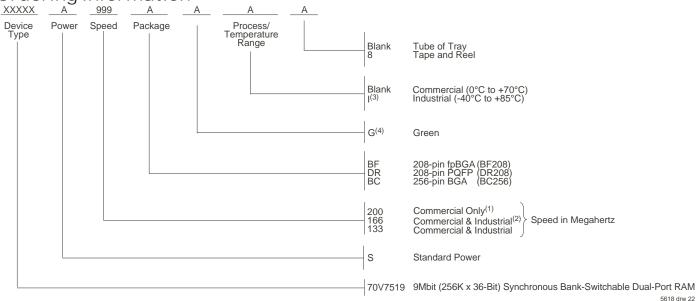
2. Device inputs = All device inputs except TDI, TMS, TRST, and TCK.

3. The Boundary Scan Descriptive Language (BSDL) file for this device is available on the IDT website (www.idt.com), or by contacting your local IDT sales representative.

High-Speed 256K x 36 Synchronous Bank-Switchable Dual-Port Static RAM

Industrial and Commercial Temperature Ranges

Ordering Information



NOTES:

- 1. Available in BC256 package only.
- 2. Industrial Temperature at 166Mhz not available in BF208 package.
- $\label{eq:contact} 3. \quad \mbox{Contact your local sales office for industrial temp range for other speeds, packages and powers.}$
- Green parts available. For specific speeds, packages and powers contact your local sales office. LEAD FINISH (SnPb) parts are in EOL process. Product Discontinuation Notice - PDN# SP-17-02

Datasheet Document History:

10/19/01: Pa	age 2, 3 & 4 Added date revision for pin configurations
Pa	age 9 Changed Isb3 values for commercial and industrial DC Electrical Characteristics
Pa	age 11 Changed to Evalue in AC Electrical Characteristics, please refer to Errata #SMEN-01-05
Pa	age 20 Increased tucp from 20ns to 25ns, please refer to Errata #SMEN-01-04
Pa	age 1 & 22 Replaced ™ logo with ® logo
01/11/02: Pa	age 2 Corrected BF-208 pinout configuration fpBGA A15
03/18/02: Pa	age 1, 9, 11 & 22 Added 200MHz specification
Pa	age 9 Tightened power numbers in DC Electrical Characteristics
Pa	age 14 Changed waveforms to show INVALID operation from opposite ports if $tco < minimum$ specified
Pa	age 1 - 22 Removed "Preliminary" status
12/04/02: Pa	age 9, 11 & 22 Designated 200Mhz speed grade available in BC-256 package only
01/16/04: Pa	age 11 Added byte enable setup time and byte enable hold time parameters and values to all speed grades in the AC Electrical
Ch	naracteristicsTable
07/25/08: Pa	age 9 Corrected a typo in the DC Chars table
01/29/09: Pa	age 22 Removed "IDT" from orderable part number
06/04/15: Pa	age 1 Added Green availability to Features
Pa	age 2, 3, 4 & 22 The package codes for BF-208 changed to BF208, BC-256 changed to BC256, and DR-208 changed to
	DR208 respectively to match the standard package codes
Pa	age 2 , 3 & 4 Removed the date from all of the pin configurations BF208, BC256 & DR208
Pa	age 22 Added Green and T&R indicators and the correlating footnotes to Ordering Information
06/22/18: Pr	oduct Discontinuation Notice - PDN# SP-17-02
La	ist time buy expires June 15, 2018



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